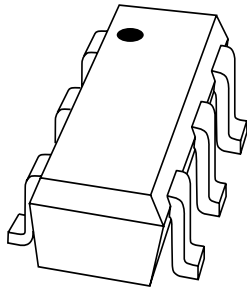


DATA SHEET



BC857BS PNP general purpose double transistor

Product specification
Supersedes data of 1997 Jul 09

1999 Apr 26

PNP general purpose double transistor

BC857BS

FEATURES

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and boardspace
- No mutual interference between the transistors.

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

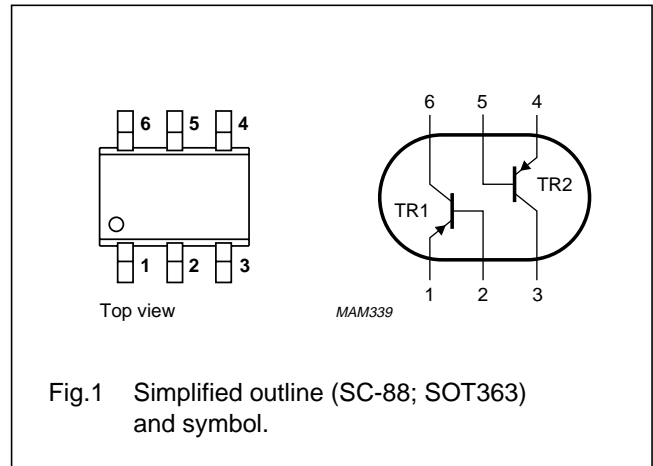
PNP double transistor in an SC-88; SOT363 plastic package. NPN complement: BC847BS.

MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| BC857BS | 3Ft |

PINNING

| PIN | DESCRIPTION |
|------|--------------------|
| 1, 4 | emitter TR1; TR2 |
| 2, 5 | base TR1; TR2 |
| 6, 3 | collector TR1; TR2 |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------------------|-------------------------------|--|------|------|------------------|
| Per transistor | | | | | |
| V_{CBO} | collector-base voltage | open emitter | – | –50 | V |
| V_{CEO} | collector-emitter voltage | open base | – | –45 | V |
| V_{EBO} | emitter-base voltage | open collector | – | –5 | V |
| I_C | collector current (DC) | | – | –100 | mA |
| I_{CM} | peak collector current | | – | –200 | mA |
| I_{BM} | peak base current | | – | –200 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ }^\circ\text{C}$ | – | 200 | mW |
| T_{stg} | storage temperature | | –65 | +150 | $^\circ\text{C}$ |
| T_j | junction temperature | | – | 150 | $^\circ\text{C}$ |
| T_{amb} | operating ambient temperature | | –65 | +150 | $^\circ\text{C}$ |
| Per device | | | | | |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1 | – | 300 | mW |

Note

1. Device mounted on an FR4 printed-circuit board.

PNP general purpose double transistor

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-------------------|---|------------|-------|------|
| Per device | | | | |
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | note 1 | 416 | K/W |

Note

1. Device mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

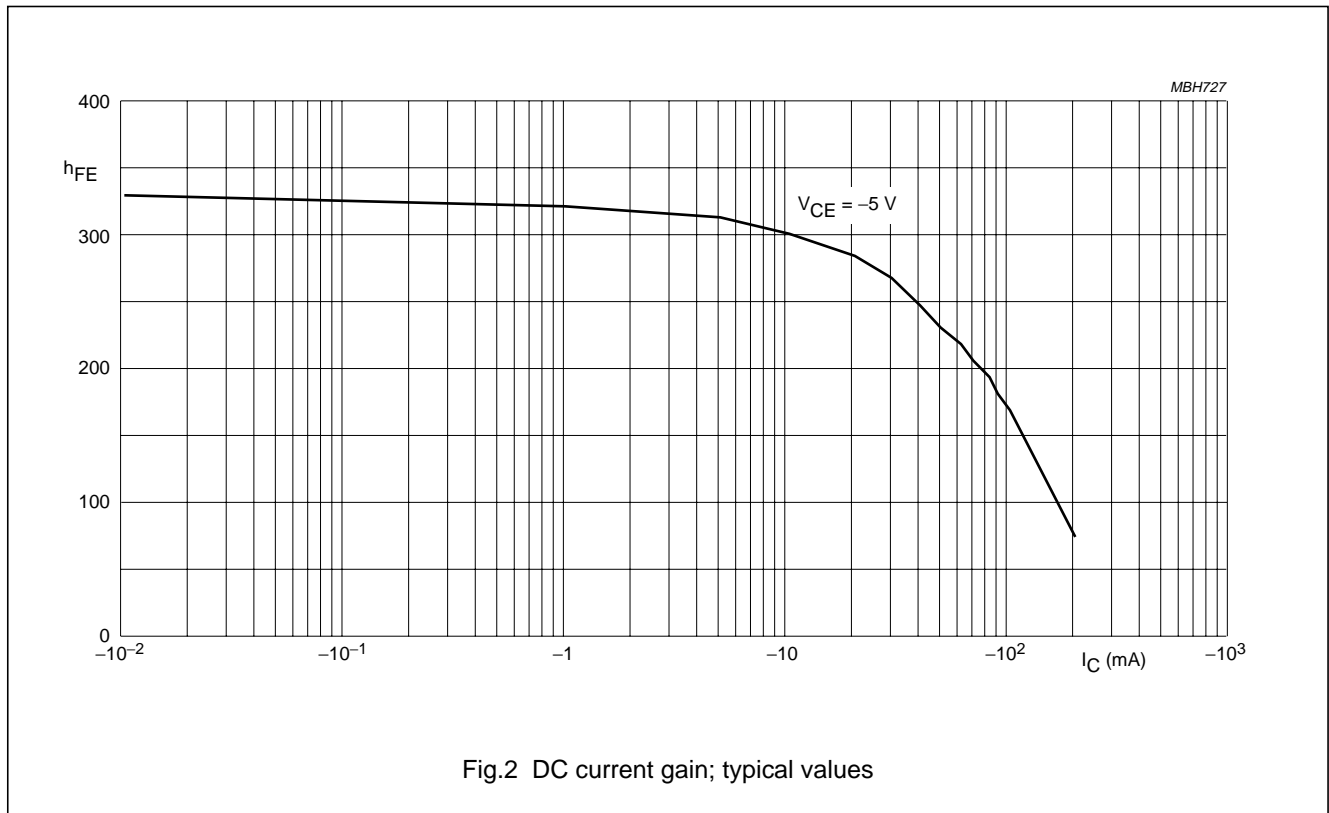
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------------|--------------------------------------|---|------|------|------|---------------|
| Per transistor | | | | | | |
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = -30\text{ V}$ | – | – | –15 | nA |
| | | $I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$ | – | – | –5 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = -5\text{ V}$ | – | – | –100 | nA |
| h_{FE} | DC current gain | $I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$ | 200 | – | 450 | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$ | – | – | –100 | mV |
| | | $I_C = -100\text{ mA}; I_B = -5\text{ mA}; \text{note 1}$ | – | – | –400 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$ | – | –755 | – | mV |
| V_{BE} | base-emitter voltage | $I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$ | –600 | –655 | –750 | mV |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$ | – | – | 2.2 | pF |
| C_e | emitter capacitance | $I_C = i_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$ | – | 10 | – | pF |
| f_T | transition frequency | $I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$ | 100 | – | – | MHz |

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

PNP general purpose double transistor

BC857BS



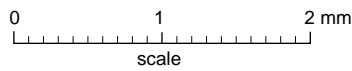
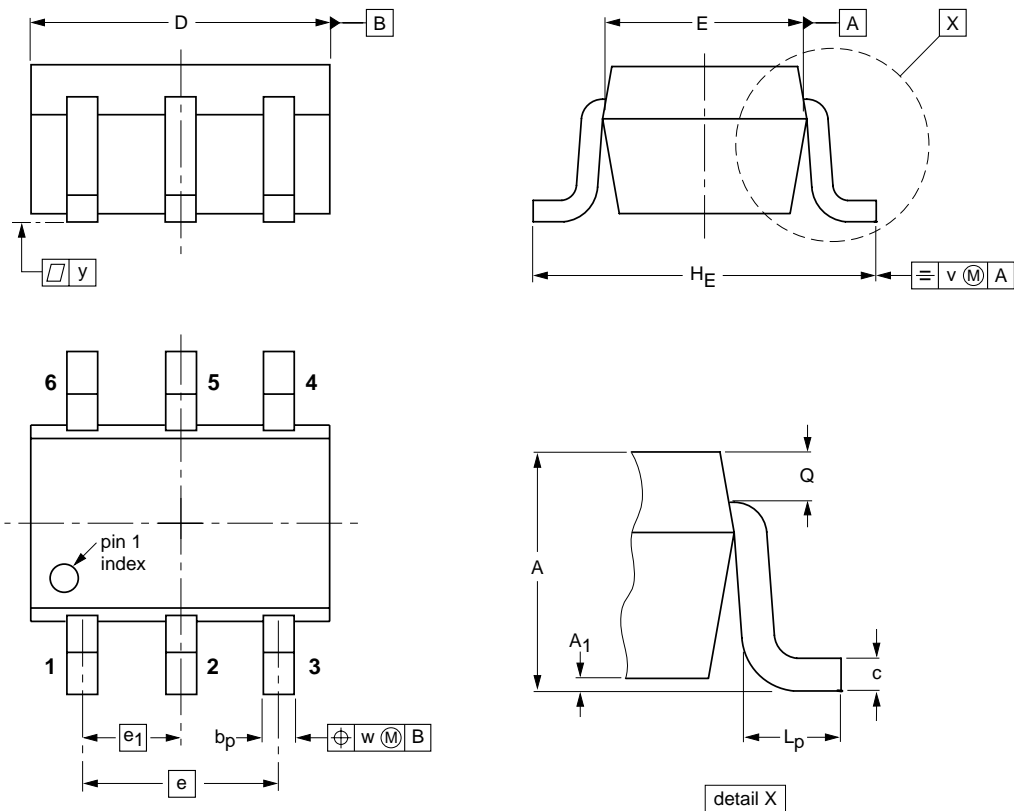
PNP general purpose double transistor

BC857BS

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ max | b _p | c | D | E | e | e ₁ | H _E | L _p | Q | v | w | y |
|------|------------|--------------------|----------------|--------------|------------|--------------|-----|----------------|----------------|----------------|--------------|-----|-----|-----|
| mm | 1.1 0.8 | 0.1 | 0.30 0.20 | 0.25 0.10 | 2.2 1.8 | 1.35 1.15 | 1.3 | 0.65 | 2.2 2.0 | 0.45 0.15 | 0.25 0.15 | 0.2 | 0.2 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|-------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT363 | | | SC-88 | | | 97-02-28 |

PNP general purpose double transistor

BC857BS

DEFINITIONS

| | |
|---|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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PNP general purpose double transistor

BC857BS

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Printed in The Netherlands

115002/00/02/pp8

Date of release: 1999 Apr 26

Document order number: 9397 750 05804

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